

## R-C Thermal Model Parameters

### DESCRIPTION

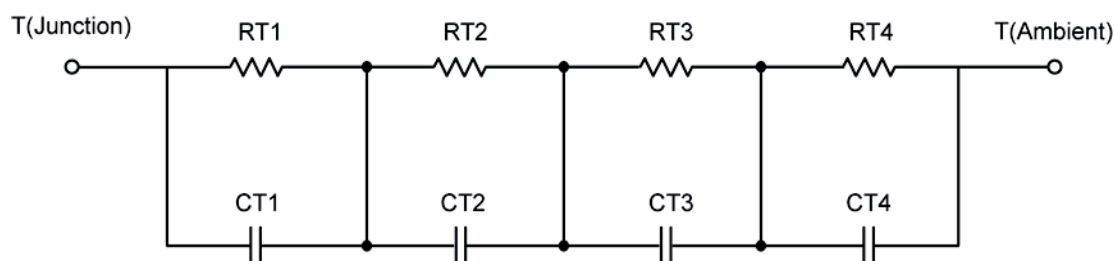
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

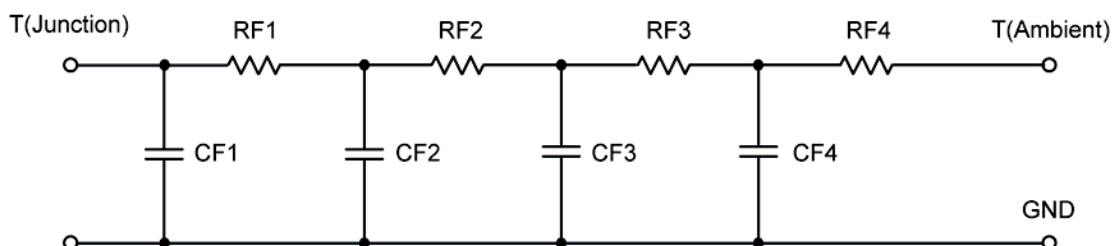
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	10.4243	N/A	9.2733
RT2	12.0158	N/A	2.8176
RT3	2.1446	N/A	890.2929 m
RT4	25.0707	N/A	7.0904
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	7.5455 m	N/A	1.1282 m
CT2	69.3500 m	N/A	254.0526 u
CT3	522.4490 u	N/A	2.8838
CT4	2.5535	N/A	4.5365 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	2.3046	N/A	4.1709
RF2	12.6154	N/A	12.1067
RF3	10.5498	N/A	2.7273
RF4	24.2231	N/A	996.1180 m
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	409.6697 u	N/A	172.6501 u
CF2	6.2604 m	N/A	842.7430 u
CF3	76.6856 m	N/A	6.8355 m
CF4	2.5913	N/A	1.3016

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

